FIG. 8

```
800  Pattern fins on a substrate
        │
        ▼
802  Form a first gate oxide on the fins
        │
        ▼
804  Protect first fins using a mask
        │
        ▼
806  Remove the first gate oxide
     from unprotected second fins
        │
        ▼
808  Form an additional gate oxide on the
     second fins and on the first gate oxide
     that covers the first fins
        │
        ▼
810  Dope ends of the fins to form source
     and drain regions
        │
        ▼
812  Form a gate conductor over the
     channel regions
```